

In the claims:

Please amend the claims as follows:

Sub J27v 17. (Amended) The apparatus of claim [8] ~~16~~ wherein said laser is placed outside said chamber, said chamber having a window through which said rectangular shaped laser beam having an elongated cross section is introduced into said chamber.

Sub J27v 21
28. (Amended) The apparatus of claim ~~25~~ ²¹ wherein [said infrared light is irradiated to said semiconductor layer in] an atmosphere in which said semiconductor layer is placed in said light processing apparatus [containing] contains nitrogen, ammonia, nitrous oxide or oxygen.

Sub J27v 29. (Amended) The apparatus of claim ~~26~~ ²⁵ wherein [said infrared light is irradiated to said semiconductor layer in] an atmosphere in which said semiconductor layer is placed in said light processing apparatus [containing] contains nitrogen, ammonia, nitrous oxide or oxygen.

Sub J27v 30. (Amended) The apparatus of claim 16 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a

silicon oxide layer formed on said semiconductor layer.

16 10
81. (Amended) The apparatus of claim 56 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

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82. (Amended) The apparatus of claim 74 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

J10 21
13 83. (Amended) The apparatus of claim 75 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

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84. (Amended) The apparatus of claim 76 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

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85. (Amended) The apparatus of claim 77 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a

~~10~~ CMT. silicon oxide layer formed on said semiconductor layer.

~~9~~ 86. (Amended) The apparatus of claim ~~16~~ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~14~~ 87. (Amended) The apparatus of claim ~~56~~ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~12~~ ~~18~~ 88. (Amended) The apparatus of claim ~~74~~ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~18~~ 89. (Amended) The apparatus of claim ~~75~~ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~18~~ 90. (Amended) The apparatus of claim ~~76~~ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~21~~ 91. (Amended) The apparatus of claim ~~77~~ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.